

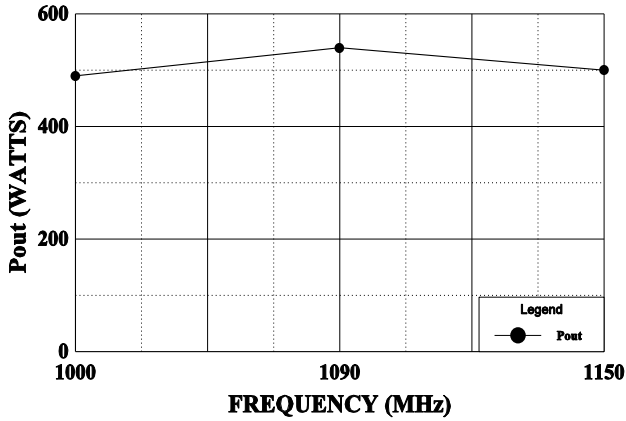




**GHZ TECHNOLOGY**  
RF-MICROWAVE SILICON POWER TRANSISTORS

**POWER OUTPUT**

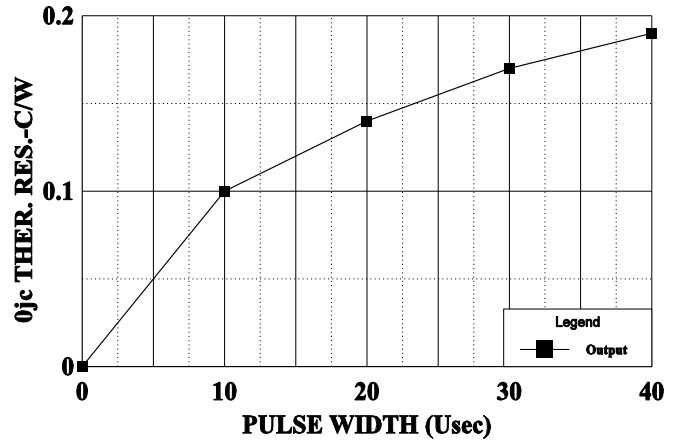
Vcc = 50 V, Pin = 125 W Peak



**DME 500**

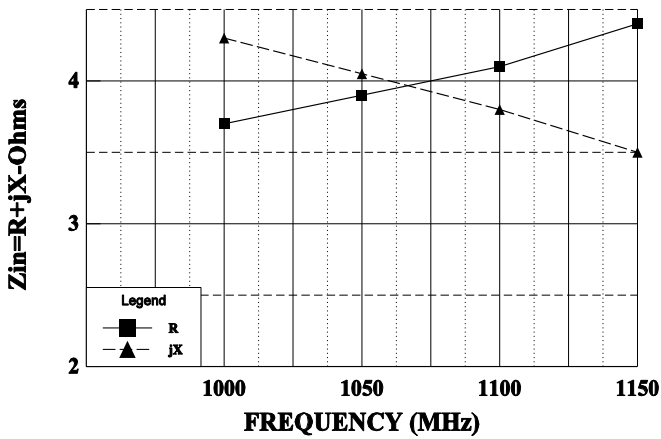
**THERMAL RESISTANCE vs PULSE WIDTH**

Vcc = 50 V, Tf = 30 C



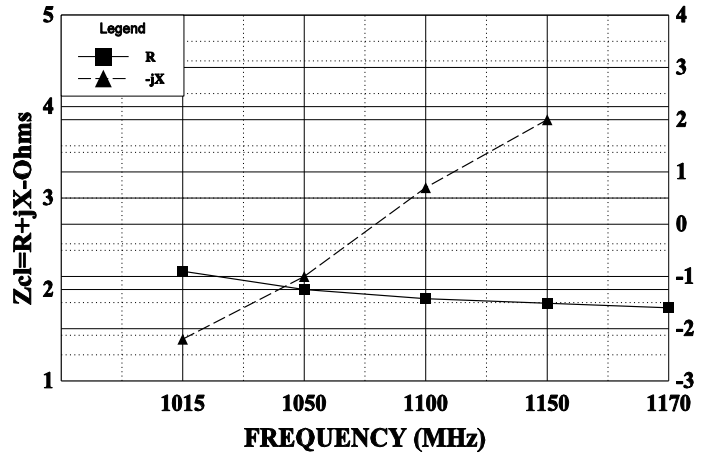
**SERIES INPUT IMPEDANCE vs FREQUENCY**

Vcc = 50 V, Po = 250 W



**SERIES LOAD IMPEDANCE vs FREQUENCY**

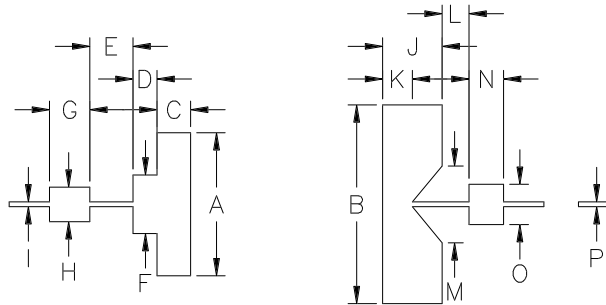
Vcc = 50 V, Po = 500 W



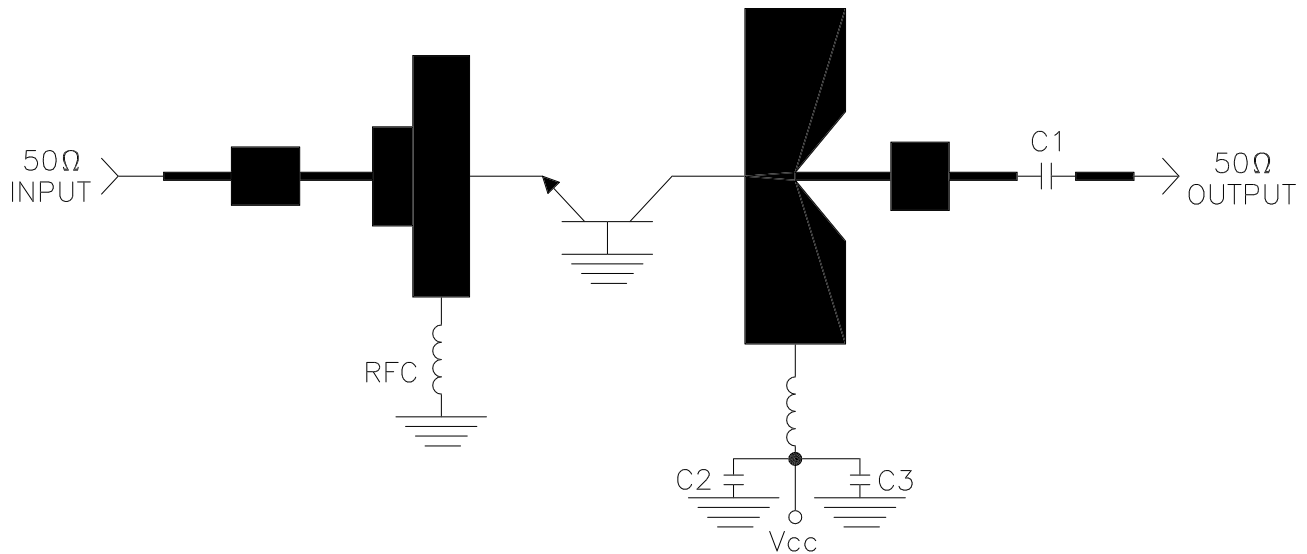
REVISIONS

ZONE	REV	DESCRIPTION	DATE	APPROVED
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DIM	INCHES
A	.745
B	1.035
C	.175
D	.125
E	.225
F	.305
G	.210
H	.180
I	.025
J	.310
K	.155
L	.140
M	.400
N	.180
O	.210
P	.025



1025/1150 MHz TEST AMPLIFIER



— = Microstrip line on E10, t=0.025"  
 C1, C2 = 82PF chip capacitor  
 C3 = 500μ Fdc @ 75V capacitor